

DATA SHEET

PMBF170

**N-channel enhancement mode
vertical D-MOS transistor**

Product specification
File under Discrete Semiconductors, SC13b

April 1995

N-channel enhancement mode vertical D-MOS transistor

PMBF170

DESCRIPTION

N-channel enhancement mode vertical D-MOS transistor in a SOT23 envelope. Designed for use as a Surface Mounted Device (SMD) in thin and thick-film circuits with applications in relay, high-speed and line transformer drivers.

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	60 V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20 V
Drain current (DC)	I_D	max.	250 mA
Total power dissipation up to $T_{amb} = 25\text{ }^\circ\text{C}$	P_{tot}	max.	300 mW
Drain-source on-resistance $I_D = 200\text{ mA}; V_{GS} = 10\text{ V}$	$R_{DS(on)}$	typ.	2.5 Ω
		max.	5.0 Ω
Transfer admittance $I_D = 200\text{ mA}; V_{DS} = 10\text{ V}$	$ Y_{fs} $	min.	100 mS
		typ.	200 mS

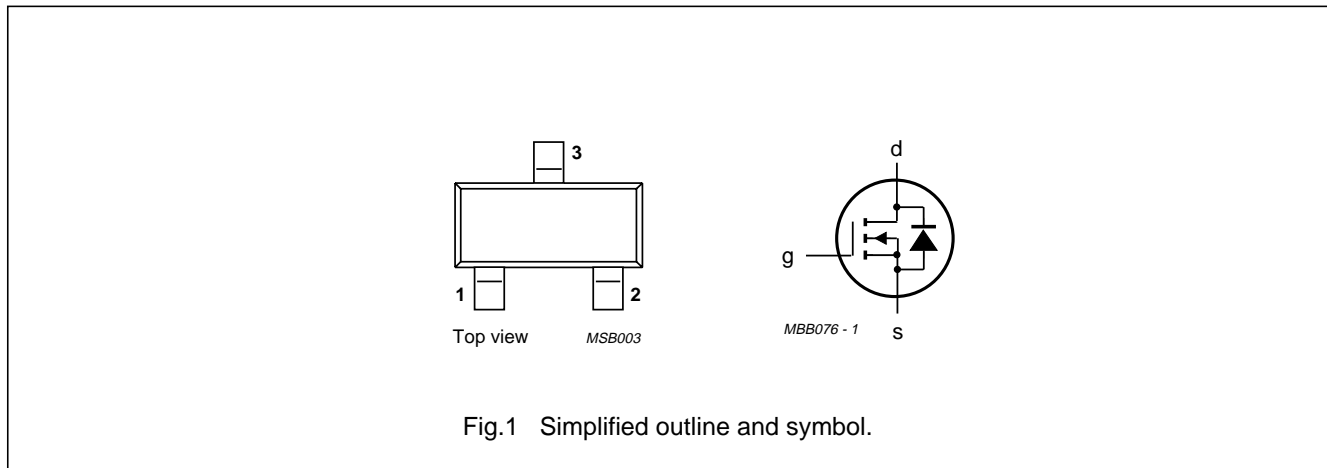
PINNING - SOT23

- 1 = gate
- 2 = source
- 3 = drain

Marking code:

PMBF170 = PKX

PIN CONFIGURATION



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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	60 V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20 V
Drain current (DC)	I_D	max.	250 mA
Drain current (peak)	I_{DM}	max.	500 mA
Total power dissipation up to $T_{amb} = 25\text{ °C}$ (note 1)	P_{tot}	max.	300 mW (note 1) 250 mW (note 2)
Storage temperature range	T_{stg}		-65 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j-a}$	=	430 K/W
From junction to ambient (note 2)	$R_{th\ j-a}$	=	500 K/W

Notes

1. Mounted on ceramic substrate measuring 10 mm × 8 mm × 0.7 mm.
2. Mounted on printed-circuit board.

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified

Drain-source breakdown voltage

$I_D = 10\text{ }\mu\text{A}; V_{GS} = 0$

$V_{(BR)DSS}$	min.	60 V
	typ.	90 V

Drain-source leakage current

$V_{DS} = 25\text{ V}; V_{GS} = 0$

I_{DSS}	max.	500 nA
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$V_{DS} = 48\text{ V}; V_{GS} = 0$

I_{DSS}	max.	1 μA
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Gate-source leakage current

$V_{GS} = 15\text{ V}; V_{DS} = 0$

I_{GSS}	max.	10 nA
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Gate-source cut-off voltage

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

$V_{GS(th)}$	min.	0.8 V
	max.	3.0 V

Drain-source on-resistance

$I_D = 200\text{ mA}; V_{GS} = 10\text{ V}$

$R_{DS(on)}$	typ.	2.5 Ω
	max.	5.0 Ω

Transfer admittance

$I_D = 200\text{ mA}; V_{DS} = 10\text{ V}$

$ Y_{fs} $	min.	100 mS
	typ.	200 mS

Input capacitance

$V_{DS} = 10\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

C_{iss}	typ.	25 pF
	max.	40 pF

Output capacitance

$V_{DS} = 10\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

C_{oss}	typ.	22 pF
	max.	30 pF

Feedback capacitance

$V_{DS} = 10\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

C_{rss}	typ.	6 pF
	max.	10 pF

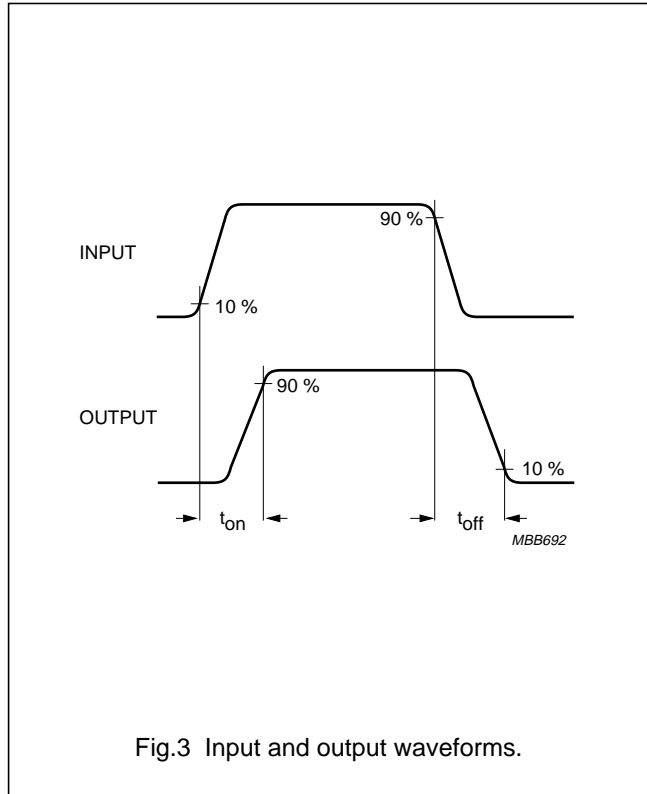
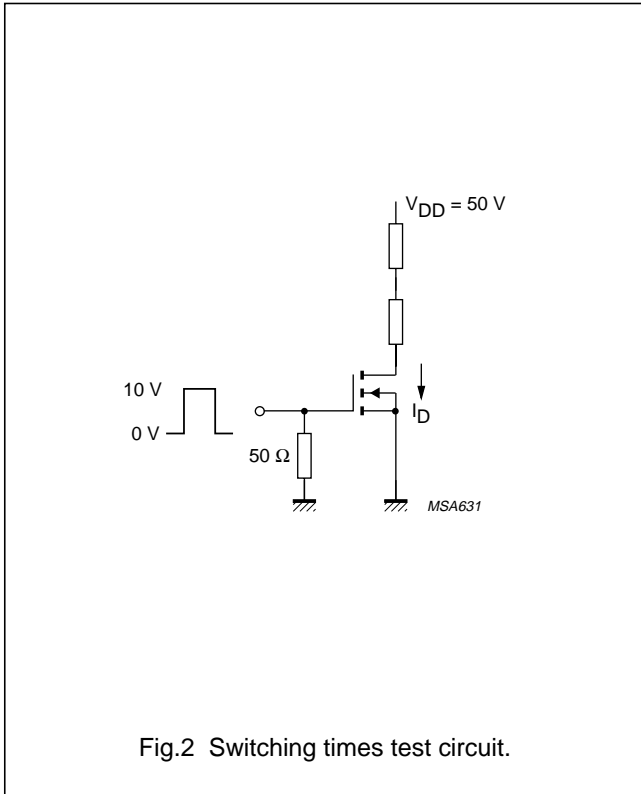
Switching times

$V_{GS} = 0\text{ to }10\text{ V}; I_D = 200\text{ mA}; V_{DD} = 50\text{ V}$

t_{on}	max.	10 ns
t_{off}	max.	15 ns

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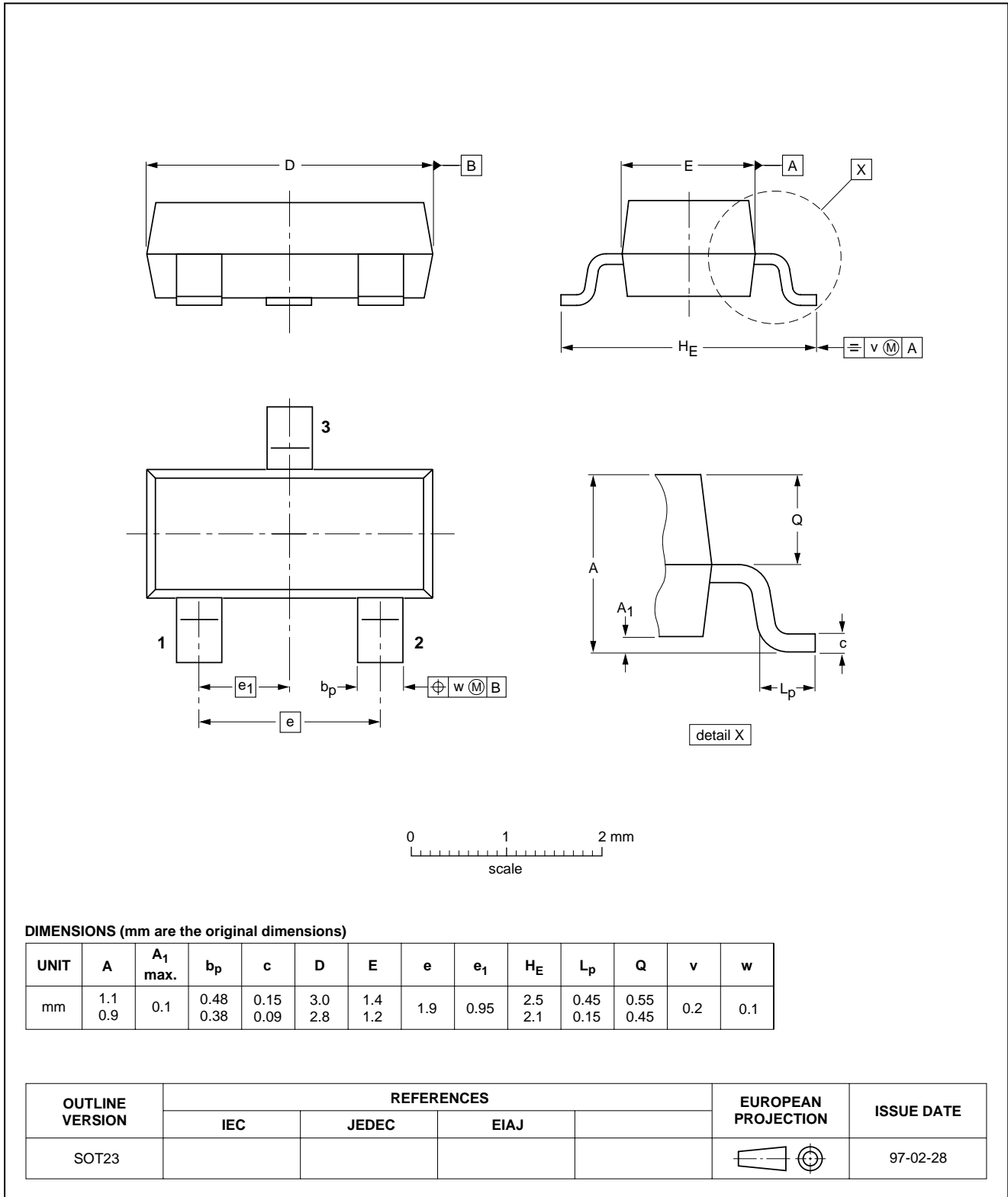
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PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT23



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PMBF170**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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